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Keywords (separated by '-')	Molecular machines - STM - Semiconductors - Activation - Molecular interaction - Switch	



# Single Molecular Machines on Semiconductor Surfaces

Younes Makoudi, Frank Palmino and Frédéric Chérioux

**Abstract** The development of nanomachines is a key challenge for the future electronics, energy conversion, biology, and medicine. Semiconductor surfaces have been one of the basic elements of many technologies for 40 years. However, despite their promising interest, semiconductor-based nanomachines are almost unstudied. In this work, a panel of single nanomachines-based semiconductor surfaces is described. The role of molecule–surface interaction for the development of nanomachines is highlighted.

**Keywords** Molecular machines · STM · Semiconductors · Activation · Molecular interaction · Switch

## 1 Introduction

The formation and control of artificial molecular nanomachines adsorbed onto a surface are two of the most promising challenges in nanotechnology [1–6]. Most of the studies on surface-mounted nanomachines by STM have been achieved on noble metal substrates. Nevertheless, from the viewpoint of future hybrid organic/inorganic molecular devices, while molecular interaction with metallic substrates is better understood, semiconducting interfaces are natural choices due to their wide-range acceptability by the industry. In this chapter, we propose to review some proof of concept of single molecular machines on semiconductor surfaces. The development and fabrication as well as the activation of nanomachines are described. The role of molecule–surface interaction is described in detail due to its important role for the achievement of molecular machines on semiconductors.

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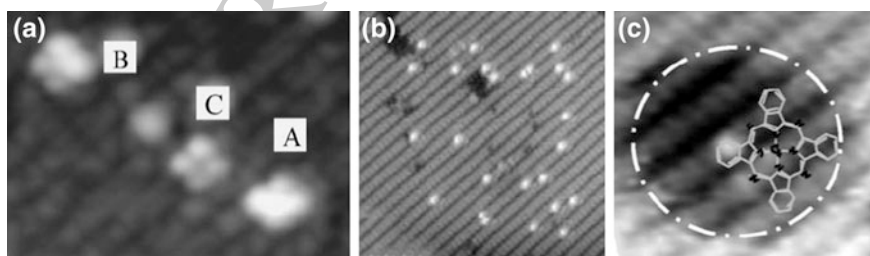
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## 2 Molecular Motions

### 2.1 1D Molecular Rotation

Semiconductor surfaces in ultra-high vacuum are well known to interact strongly with organic molecules. For example, on Si surfaces, several dangling bonds can lock the molecules adsorbed onto the surface. To circumvent this problem, we need to use a less reactive surface. In the case of molecular rotation, one of the possibilities is to anchor the molecule to only one dangling bond acting as a rotation axis. This idea has been developed on Si(100)- $2 \times 1$  surface with metal phthalocyanine molecules (MPc) [7, 8]. The authors have shown by STM that on the Si(100)- $2 \times 1$  reconstruction, CoPc and CuPc are bound to the surface via their central metal atom. In these conditions, the molecules, parallel to the surface, are in a stationary position (Fig. 1a). To induce a rotation via a single dangling bond, the surface must be, in a first step, passivated. The Si(100)- $2 \times 1$  H-passivated surface is achieved by the exposure of the initial substrate to  $1 \times 10^{-6}$  Torr of hydrogen for 10 min with a hot tungsten filament. Subsequently, isolated dangling bonds are created by feedback control lithography (FCL) using the STM tip to induce the desorption of one hydrogen atom (Fig. 1b).

After evaporation of MPc onto this surface, the 4-lobe structures previously observed were not detected but circular depression with a double diameter of CoPc is observed. This is assigned to one MPc molecule bound to the surface through its outer benzene ring and rotating as depicted in Fig. 1c. A molecular modeling study confirmed that bonding between the benzene ring and the surface induces the lowest adsorption energy. Due to the hydrogen-passivated surface, the adsorption energy difference for different angles around the rotation axis is negligible compared to  $kT$ . In these conditions, the CoPc molecule rotates easily around the benzene ring.



**Fig. 1** **a** STM CoPc image on Si(100)- $2 \times 1$  surface ( $V_s = -2.5$  V,  $I_t = 0.2$  nA) showing three different configurations. No rotation is observed. **b** Si(100)- $2 \times 1$ :H surface where the *bright* protrusions correspond to dangling bonds made by FCL ( $V_s = -3$  V,  $I_t = 0.2$  nA). **c** Schematic view of CoPc anchored to a dangling bond via one of its benzene rings and rotated around this benzene ring ( $V_s = -2$  V,  $I_t = 0.2$  nA). Reprinted with permission from [8]

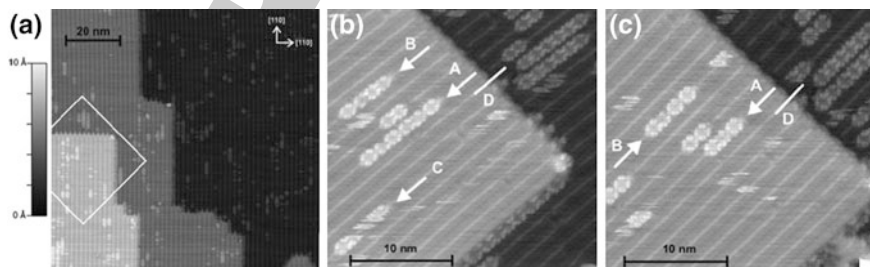
## 2.2 1D Molecular Sliding on InSb

Thermally activated motion often leads to a molecular Brownian motion [4]. To control the direction of the motion, the use of 1D periodic surfaces or step edges is a good choice to induce a linear movement. Contrary to metallic surfaces, which offer few possibilities to obtain 1D periodic surfaces (Cu–O/Cu [9] or Au(111) [10]), semiconductor or metal–semiconductor interfaces possess a high number of 1D surface reconstructions [11–14]. Few of them have been tested for molecular motion; nevertheless, the results obtained on InSb or SmSi are very convincing. In each case, we can note that the adsorption site as well as the matching between the surface unit-cell dimension and the molecular dimensions is a crucial factors to obtain good conditions for the achievement of matter transport.

The InSb(001)  $\sqrt{2} \times \sqrt{2}$  reconstructed surface is strongly anisotropic and constituted by In chains in the top adlayer. Molecular diffusion along the chains has been observed with PbPc [15, 16], a non-planar phthalocyanine, as well as CuPc [17], a planar molecule. On the CuPc/InSb(001) interface, CuPc molecules are adsorbed along the step edges and on the terraces (Fig. 2).

Along the step edges, in the [1-10] direction, the molecules are very weakly bound to the surface and appear like two protrusions, while in the [110] direction, the molecules are strongly bound to the surface and no change is observed after several scans. On terraces, some noisy horizontal lines indicate mobile molecules while CuPc molecules appear as eight separated protrusions centered over the bright substrate rows, which correspond to the topmost In atoms. CuPc molecules form chains constituted by a few molecules, which diffuse between two frames. These room temperature STM observations show the high mobility of the molecules along the [110] direction. Based on symmetry considerations, an adsorption model is proposed in Fig. 3.

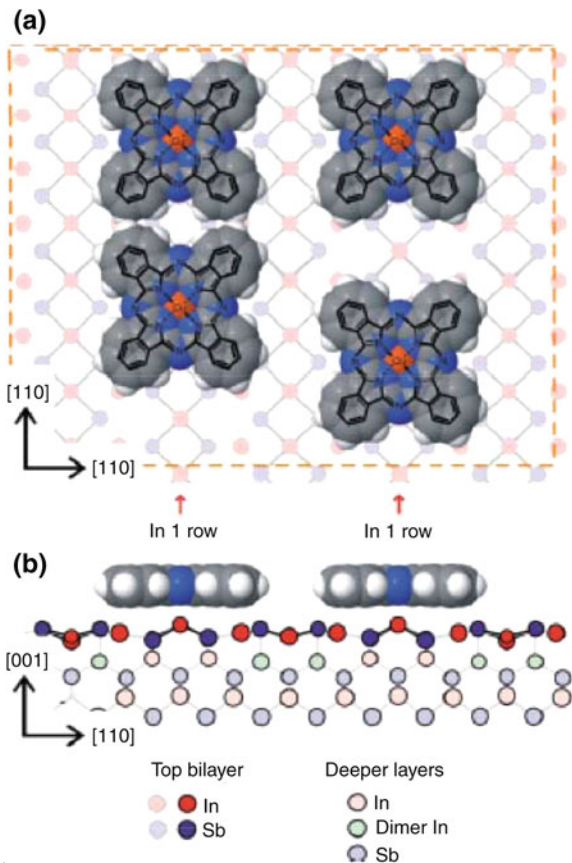
Two interactions are suggested between molecules and the surface: one between the Cu atom and the In adlayer atom, and the second one between the nitrogen atoms and the In adlayer atom.



**Fig. 2** **a** Large-scale STM image of CuPc/InSb(001) interface  $(100)c(8 \times 2\sqrt{2}) \times 100 \text{ nm}^2$ ,  $V_s = -1 \text{ V}$ ,  $I_t = 0.3 \text{ nA}$ ). The white frame indicates the area scanned and shown in **b** and **c**. **b** and **c** show CuPc molecular diffusion between two STM frames ( $30 \times 30 \text{ nm}^2$ ,  $V_s = -1 \text{ V}$ ,  $I_t = 0.15 \text{ nA}$ ). Reprinted with permission from [17]



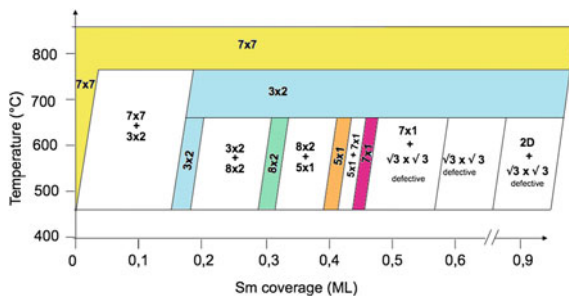
**Fig. 3** Adsorption model **a** top view and **b** side view of CuPc on InSb(001)c( $8 \times 8$ ) reconstruction. The copper atom is always positioned over the In adlayer atom. A major interaction is possible between In and nitrogen atoms. Reprinted with permission from [17]



### 2.3 1D Molecular Sliding on Rare Earth Silicides

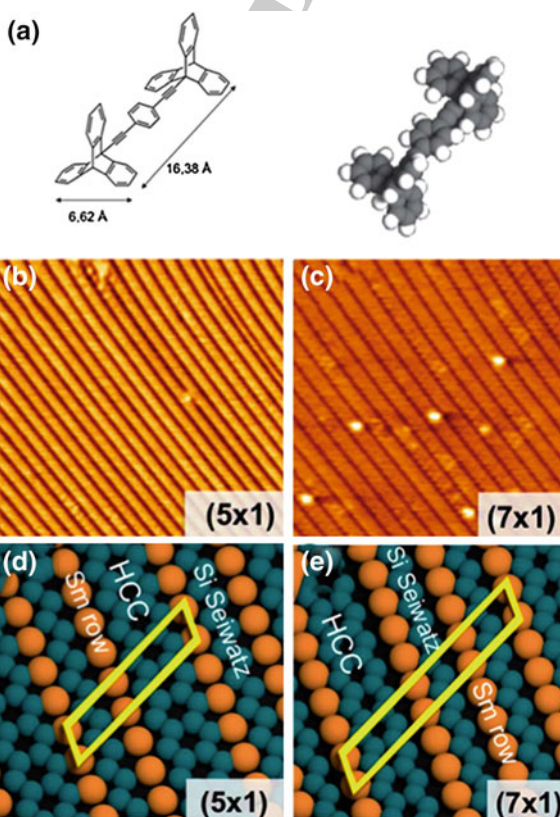
Due to their low lattice mismatch and their valence changes, rare earth silicides on Si(111) induce a high number of reconstructions depending on rare earth coverage and annealing temperature. In particular, the SmSi(111) interface possesses a complex surface phase diagram with four different 1D reconstructions in the submonolayer range (Fig. 4) [18]. These reconstructions are based on a combination of Si honeycomb chain channels (HCCs), Si Seiwatz chains, and Sm rows. They appear like large stripes on the STM images (Fig. 5 b, c). The main interest of these reconstructions with similar electronic properties is the possibility to adapt the periodicity of the unit cell ( $\times 3$ ,  $\times 5$ ,  $\times 7$ , or  $\times 8$ ) to the molecular dimensions.

The 1,4-di(9-ethynyl)triptycene)benzene molecule (DETB) (Fig. 5a) has been used to study the directional molecular sliding on the ( $8 \times 2$ ), the ( $5 \times 1$ ), and the ( $7 \times 1$ ) reconstructions described in Fig. 5 b–e [13, 19]. This molecule has been chosen because the distance of 1.64 nm between two Sm rows of SmSi interface corresponds to the length of the molecule.



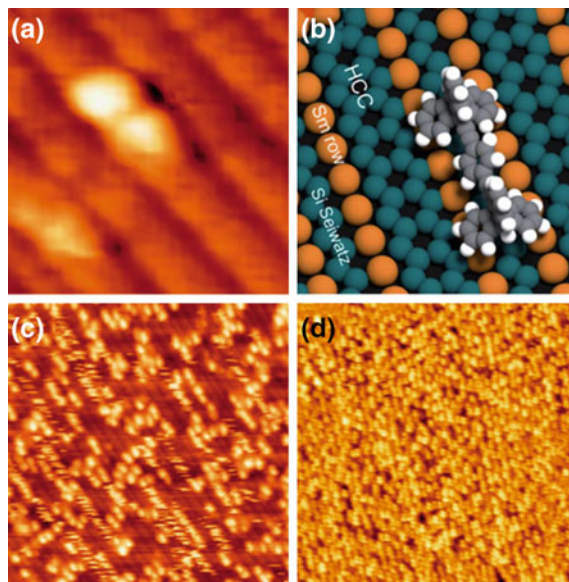
**Fig. 4** Surface phase diagram of SmSi(111) interfaces. The  $(3 \times 2)$ ,  $(8 \times 2)$ ,  $(5 \times 1)$ , and  $(7 \times 1)$  are 1D reconstructions in the submonolayer Sm coverage

**a** The 1,4-dimethyl-2,3,5-trisubstituted benzene molecule (DET<sub>B</sub>). **b–e** STM images ( $32 \times 32 \text{ nm}^2$ ,  $V_s = 2 \text{ V}$ ,  $I_t = 0.18 \text{ nA}$ ) and structural models of both  $(5 \times 1)$  and  $(7 \times 1)$  reconstructions. Reprinted with permission from [19]



96 On the SmSi(111)- $5 \times 1$  reconstruction at room temperature, the DETB appears  
 97 on STM images like two paired protrusions attributed to the two triptycene.  
 98 All the DETB molecules are adsorbed onto the large stripes and are self-aligned  
 99 along the  $[1-10]$  direction with the triptycene wheels above two Sm chains as  
 100 described in Fig. 6b. Some noisy lines, corresponding to molecular diffusion, are





**Fig. 6** **a** Isolated DETB molecule on SmSi-(5 × 1) × 7 nm<sup>2</sup>,  $V_s = 1.8$  V,  $I_t = 0.7$  nA. **b** DETB adsorption model on (5 × 1) reconstruction. **c** Interface for 0.3 monolayer molecule coverage. Noisy stripes correspond to DETB diffusion along Sm rows. **d** Interface for 0.9 monolayer molecule coverage showing the self-alignment after the surface diffusion. Reprinted with permission from [19]

101 observed along the stripes and prove that the movement is guided by a strong  
 102 template effect of the surface.

103 The study of the template effect of the surface on the adsorption and the diffusion  
 104 of DETB molecules has been done by Bouju et al. [19]. By using a larger unit cell, the  
 105 SmSi-(7 × 1) instead of a the SmSi-(5 × 1), they shown that the DETB molecules can  
 106 be adsorbed with a new orientation where their main axis is now perpendicular to the  
 107 Sm rows (Fig. 7a, b). In these conditions, the molecular motions induce dual frizzled  
 108 bands on the STM images (black arrows in Fig. 7) corresponding to the two-tripty-  
 109 cene wheels. A semiempirical calculation (ASED-MO) confirms that in this ori-  
 110 entation, the energy barrier is the most favorable to a sliding onto the surface and that the  
 111 DETB molecules are confined between two HCC channels.

### 112 3 Tools to Induce Molecular Motion at a Semiconductor 113 Surfaces

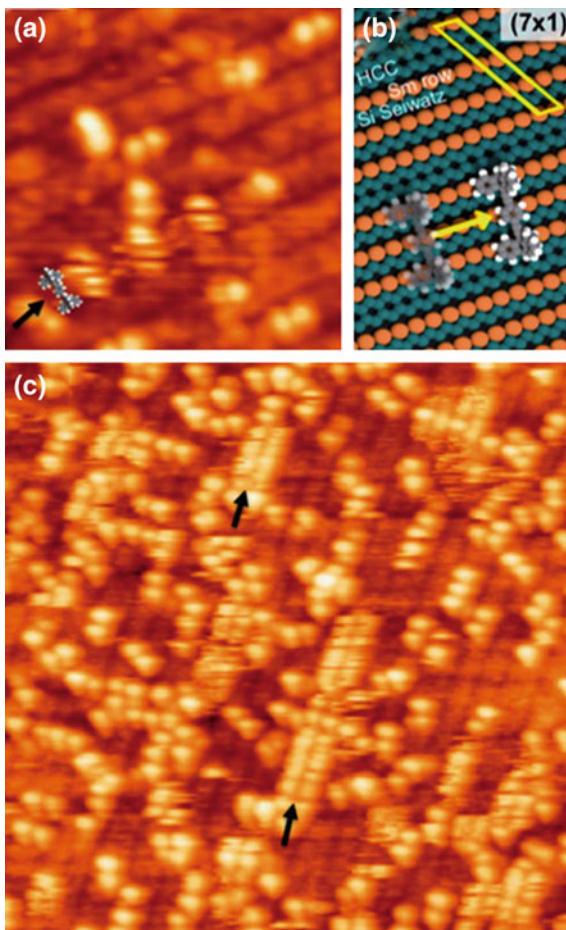
114 Self-assembly is an important tool in nanotechnology [20, 21]. In order to achieve  
 115 self-assembly growth, molecules must be free to move across a surface. However,  
 116 because of the dangling bonds, this movement is not often possible without an



**a** STM image of DETB molecules on SmSi-(7 × 1) (15 × 15 nm<sup>2</sup>,  $V_s = 1.8$  V,  $I_t = 0.02$  nA).

**b** DETB adsorption model which induces the sliding perpendicular to the Sm rows.

**c** STM image showing the DETB sliding and the formation of dual bands (*black arrows*). Reprinted with permission from [19]



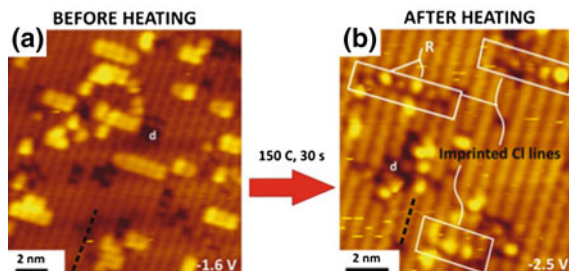
117 external intervention. The idea is to provide some energy to the system (molecule/  
 118 surface) in order to overcome molecule–surface interactions and diffusion barriers.  
 119 Three sources of energy (heat, light, or electrons) can be available in a STM  
 120 chamber and can be used to induce molecular motions on semiconductor surfaces.

121 Despite the importance of this step for the development of molecular electronics,  
 122 only very few examples dealing with the subject are available in the literature.

### 123 3.1 Heat

124 The usual and easiest method to provide energy in a STM is based on the heating of  
 125 the investigated system. Our work in this domain illustrates well the effect of  
 126 temperature in self-assembly formation [22–24]. Although molecular deposition





**Fig. 8** STM images recorded at room temperature of a Si(100)- $2 \times 8$  surface exposed to 0.04 L dose of chloropentane. **a** Before heating the surface at 150 °C during 30 s ( $V_s = -1.6$  V,  $I_t = 0.2$  nA, 1 s). **b** After heating ( $V_s = -2.5$  V,  $I_t = 0.2$  nA, 1 s). Physisorbed lines of CP are imprinted as chemisorbed lines of Cl pairs. Reprinted with permission from [25]

127 was performed at room temperature, this thermal energy was sufficient for molec-  
 128 ules to overcome diffusion barriers and then form different self-assemblies.

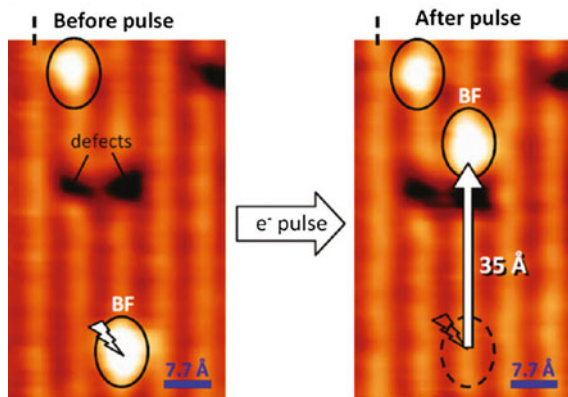
129 Heat can also be used to activate a local atomic reaction (LAR) as reported by  
 130 Harikumar et al. Indeed, LAR of the physisorbed lines of 1-chloropentane (CP)  
 131 pairs was induced by heating. Figure 8 shows representative images of physisorbed  
 132 lines of CP pairs after dosing at room temperature and after heating to 150 °C for  
 133 30 s. Some lines have completely reacted after heating and producing new lines of  
 134 pairs of Si–Cl covalent bonds.

135 This result shows that we can transform a weakly attached physisorbed pattern,  
 136 by using heat as source of energy, in order to induce chemical reaction with  
 137 semiconductor surface and so rendering the pattern permanent.

### 3.2 Electrons

139 Excitation of molecules at a surface can be achieved by the STM tip and can induce  
 140 molecular motions in four possible directions: (1) toward the surface (transition  
 141 from a physisorbed interaction to chemisorbed one) [26]; (2) away from the surface  
 142 (desorption) [27]; (3) parallel to the surface (migration, diffusion) [28]; or (4)  
 143 rotating around a point of the surface (molecular switch) [29]. The third case is the  
 144 direction favoring the self-assembly.

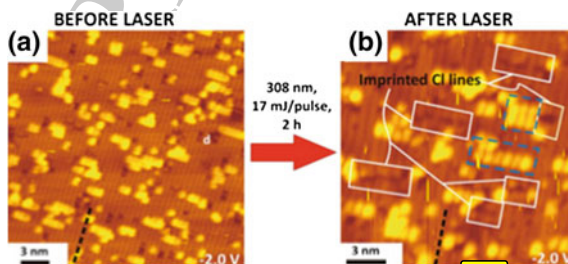
145 Harikumar et al. [30], for example, showed that electron excitation of chemi-  
 146 sorbed benzene at Si(100) causes long-range (around 48–35 Å in Fig. 9) molecular  
 147 recoil in the plane of the surface as illustrated in Fig. 9. This movement is induced  
 148 by an electron pulse ( $-2$  V, 0.2 nA, 1 s) with the STM tip and is followed by a  
 149 chemisorptive reattachment of the molecule. The migration is due to molecular  
 150 cartwheeling rotation. It is directed along the dimer rows and over a missing dimer  
 151 defect, carrying the molecules over raised surface obstacles.



**Fig. 9** Benzene migration over  $\text{Si}(100)\text{-}2 \times 1$  surface at room temperature. STM images ( $V_s = -1.5$  V,  $I_t = 0.2$  nA) of the same area *before* and *after* an electron pulse ( $V_s = -2$  V,  $I_t = 0.2$  nA, 1 s). Reprinted with permission from [30]

### 3.3 Light

Although this excitation source is widely used in air and in liquid environments [31], to our knowledge, only one example has been reported for its use in UHV and on semiconductor surfaces. This example concerns, once again, the Harikumar et al. [25] work concerning 1-chloropentane on  $\text{Si}(100)$  surface. Like in the case of heat as energy source of excitation, LAR of the physisorbed lines of CP pairs can also be induced by light. Indeed, Fig. 10 shows photo-imprinted Cl lines after 2 h of laser irradiation of physisorbed CP on  $\text{Si}(100)\text{-}2 \times 1$  surface. The photo-induced reaction is due to electrons ejected from the substrate rather than direct excitation of the molecule.



**Fig. 10** STM images recorded at room temperature of a  $\text{Si}(100)\text{-}2 \times 1$  surface exposed to 0.04 L dose of chloropentane. **a** *Before laser irradiation* ( $V_s = -2$  V,  $I_t = 0.2$  nA, 25 s). **b** *After 2 h of laser irradiation* ( $V_s = -2$  V,  $I_t = 0.2$  nA, 18 s). Physisorbed lines of CP are photo-imprinted as chemisorbed lines of Cl pairs (white rectangles). Non-reacted physisorbed CP lines are highlighted by blue broken rectangles. Reprinted with permission from [25]

## 4 Bistable Molecules as Model Systems of Molecular Machines

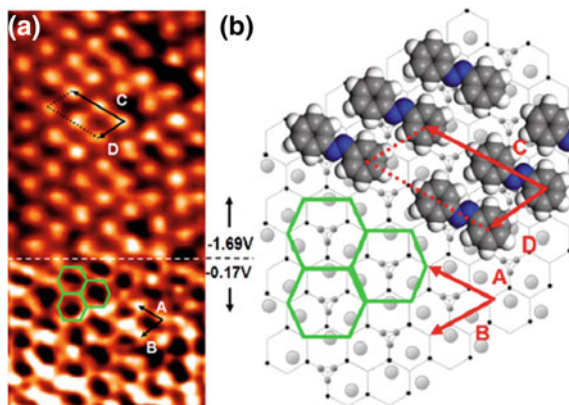
### 4.1 Adsorption of Bistable Azobenzene Molecules on Semiconductors

The most basic approach to study molecular bistability on a surface consists in the deposition of a molecule that is intrinsically bistable. Then, in a second step, one checks whether the molecular bistability is maintained or altered by the presence of the surface. Azobenzene derivatives have been deeply investigated as model system of bistable molecules in gas phase or in solution [32–37]. The presence of a N=N double bond located between two phenyl groups allows a reversible isomerization between *trans* and *cis* structural isomers (i.e., diastereoisomers). The adsorption of azobenzene derivatives has also been investigated on noble metal surfaces at low temperature (<100 K) [38–48]. The switching processes are based on the isomerization of molecules induced by an external stimulus, such as light or temperature (which are also used in gas phase or in solution experiments), inelastic tunneling electrons (IET), tip-induced molecular deformation, and electric field due to the presence of the STM junction. Semiconductor surfaces are fascinating for surface photo- or tip-induced switching due to their tunable optical and electronic properties.

The adsorption of *trans*-azobenzene (TAB) and *cis*-azobenzene (CAB) was investigated on Ag/Ge(111)- $\sqrt{3} \times \sqrt{3}$ -R30° by Wu et al. [49] at 100 K. Single TAB molecules were observed as two paired lobes on the surface. The formation of large, well-organized, and closely packed domains was achieved by increasing the coverage rate. From in situ observation of the substrate lattice, the TAB adsorption site was determined. TAB monolayer is commensurable with the substrate and forms a  $2 \times 1$  structure (Fig. 11). The driving forces of TAB monolayer growth are hydrogen bonds between TAB molecules and molecule–substrate interactions. CAB molecules have been deposited on the same surface. However, it is quite difficult to obtain pure CAB molecules because of their unstability (spontaneous isomerization). Therefore, a mixture of TAB and CAB, containing 10 % of CAB, was adsorbed on the surface. CAB molecules are adsorbed on TAB domain boundaries. CAB molecules appear as two paired lobes, one spot being brighter than the other due to one out-of-plane phenyl group. Despite many attempts, TAB photoisomerization is unsuccessful on Ag/Ge(111)- $\sqrt{3} \times \sqrt{3}$ -R30°. The absence of TAB photo-isomerization is explained by the strong TAB–surface interaction that leads to a surface energy relaxation instead of the desired isomerization process.

Decreasing the molecule–surface interactions seems to be a key point for the successful achievement of azobenzene isomerization on semiconductors. Molecule–surface interaction can be tuned by using:

- Passivated semiconductors
- Tailored molecules

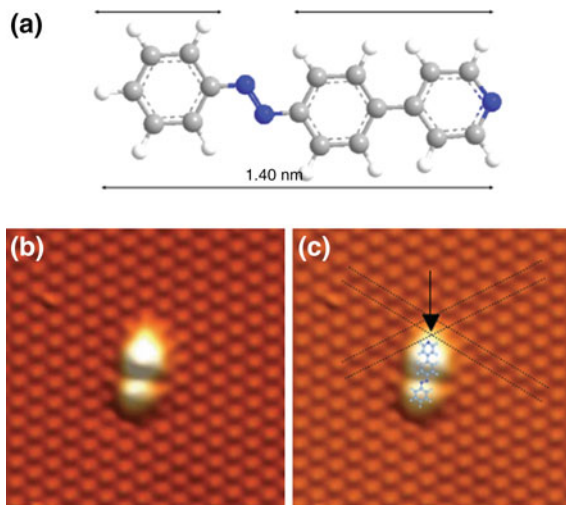


**Fig. 11** **a** STM image ( $5 \times 10 \text{ nm}^2$ ) of a TAB monolayer on  $\text{Ag}/\text{Ge}(111)\text{-}\sqrt{3} \times \sqrt{3}\text{-R}30^\circ$ . The tip bias is altered during the scan to image simultaneously the TAB molecules (upper part with  $V_s = -1.69 \text{ V}$  and  $I = 80 \text{ pA}$ ) and the hexagonal pattern of the substrate atoms (lower part with  $V_s = -0.17 \text{ V}$  and  $I = 80 \text{ pA}$ ). **b** Structural model of image shown in **a**. Reprinted with permission from [49]

203 When  $\pi$ -conjugated molecules, such as azobenzene derivatives, are deposited on  
 204 a semiconductor, the main contribution to the molecule–surface interactions is the  
 205 interaction of the molecule’s  $\pi$ -electrons and electrons of surface dangling bonds.  
 206 Recently, we have demonstrated that the molecule–surface interactions can be  
 207 controlled by using the  $\text{Si}(111)\text{-}\sqrt{3} \times \sqrt{3}\text{-R}30^\circ$  surface, noted  $\text{Si}(111)\text{-B}$ . The  
 208 silicon adatoms dangling bonds are depopulated because of the presence of a boron  
 209 atom underneath each silicon adatom, leading to a weak  $\pi$ -conjugated molecule–  
 210 surface interaction [22, 24, 50–52]. In all these cases, molecule–surface interaction  
 211 is weak enough to achieve the formation of large-scale supramolecular networks. In  
 212 order to check the feasibility of azobenzene isomerization on a  $\text{Si}(111)\text{-B}$  surface,  
 213 we tried to deposit TAB molecules on this surface. However, the observation of  
 214 single or self-assembled TAB molecules was impossible in the 100–300 K  
 215 temperature range. Another azobenzene derivative, 4-pyridylazobenzene (PAB)  
 216 molecule, has been synthesized (Fig. 12). Due to the presence of a pyridyl group,  
 217 PAB- $\text{Si}(111)\text{-B}$  interactions should be stronger than TAB- $\text{Si}(111)\text{-B}$ . A single PAB  
 218 molecule has indeed been observed on a  $\text{Si}(111)\text{-B}$  surface at room temperature.  
 219 PAB molecules appear as two paired lobes, one being longer than the other. In  
 220 empty states STM images, the interaction between the nitrogen atom lone pair and  
 221 the silicon adatom is highlighted by a bright protrusion (Fig. 12b, c) [53].

222 PAB manipulation at room temperature was successfully achieved by applying a  
 223 STM tip pulse bias voltage of 3 V during 300 ms after positioning the STM tip  
 224 above a PAB molecule (Fig. 13a).

225 In these conditions, PAB molecules switch reversibly from one state to the other,  
 226 which are mirror images of each other by a plane mirror; therefore, they are  
 227 enantiomers. No *cis*–*trans* PAB isomerization occurs on a  $\text{Si}(111)\text{-B}$  surface, and it

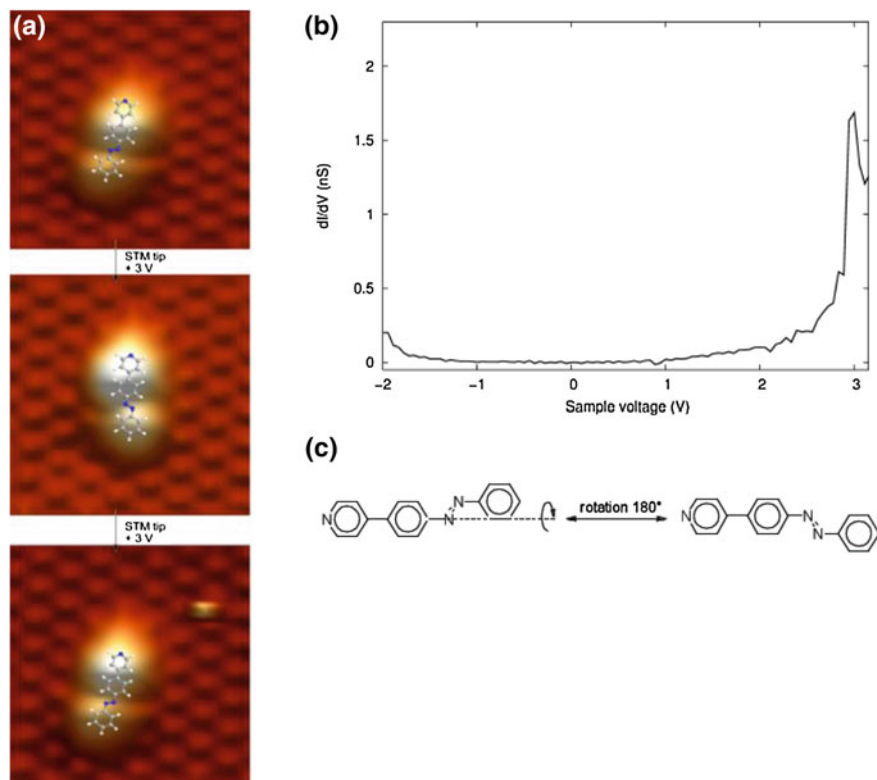


**Fig. 12** **a** Molecular structure of pyridylazobenzene (*PAB*). **b** Room temperature STM image ( $7 \times 6 \text{ nm}^2$ ,  $V_s = 1.5 \text{ V}$  and  $76 \text{ pA}$ ) of a single *PAB* molecule deposited on Si(111)-B. **c** Superimposed structural model of *PAB*/Si(111)-B. *PAB*-Si(111)-B interaction is highlighted by a black arrow. Reprinted with permission from [53]

228 is a chiral switching between two enantiomers. *PAB* is not a chiral molecule but a  
 229 prochiral molecule. The presence of the surface induces the formation of chiral  
 230 adsorbates. From a mechanistic point of view, the *PAB* chiral switching is based on  
 231 the tunneling electron transfer to *PAB* LUMO, located around 3 V (Fig. 13b),  
 232 leading to a negatively charged transient state. Then, energy transfer to molecular  
 233 vibrations leads to chiral switching by molecular rotation of the azophenyl group  
 234 around the C–N bond (Fig. 13c) instead of *cis*–*trans* isomerization. This chiral  
 235 switching is of interest in order to store information at the molecular level on a  
 236 semiconductor surface because this switching occurs reversibly at room tempera-  
 237 ture and in a controlled manner.

238 In order to observe the *cis*–*trans* isomerization of azobenzene derivatives,  
 239 Crommie et al. [54] proposed to use GaAs(110) as semiconductor surface and  
 240 3,3',5,5'-tetra-*tert*-butylazobenzene (TTB-AB) as molecules at low temperature  
 241 ( $<20 \text{ K}$ ). The (110) surface of GaAs was chosen due to the absence of surface states  
 242 within its direct band gap (1.43 eV) [55], and TTB-AB was chosen because the TTB-  
 243 AB aromatic molecular plane is held away from the surface by *tert*-butyl groups.  
 244 Formation of TTB-AB large-scale monolayer islands on GaAs(110) was achieved in  
 245 (Fig. 14a). The supramolecular network is commensurable with the surface, and  
 246 TTB-AB shows the same shape (four-lobed structure) as the one observed on noble  
 247 metals, corresponding to the *trans*-isomer [47]. TTB-AB photoswitching on GaAs  
 248 (110) was investigated by STM with UV light illumination (375 nm) during 18 h. UV  
 249 light exposure leads to morphological modifications of the TTB-AB monolayer  
 250 islands. Several bright protrusions, forming some stripes, have appeared along

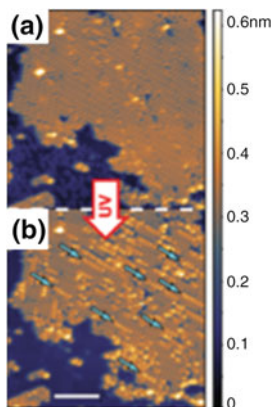




**Fig. 13** **a** Sequence of PAB manipulation by STM tip bias voltage pulse on a Si(111)-B surface with superimposed structural model on STM images. **b** Spectrum of the differential conductance,  $dI/dV$ , recorded on a PAB molecule adsorbed on a Si(111)-B surface. **c** Two PAB conformers rotated by 180° of an azophenyl group around a C–N bond. Reprinted with permission from [53]

251 preferential directions of the GaAs(110) surface (Fig. 14b). Bright protrusions have  
 252 been assigned to TTB-AB *cis*-isomers, as previously observed on noble metal surface,  
 253 due to the out-of-plane configuration of the *cis*-isomer [46].

254 On Au(111) surface, TTB-AB photoswitching is a random process because the  
 255 bright protrusions are randomly distributed on the surface [46]. In the case of GaAs  
 256 (110), formation of *cis*-isomer stripes is in favor of a cascade-like process. This very  
 257 interesting process can be explained by the reduced steric hindrance after TTB-AB  
 258 photo-isomerization. When a first *trans*-TTB-AB molecule is photo-isomerized, the  
 259 *cis*-isomer occupies a smaller area than the *trans*-isomer because *cis*-TTB-AB is out  
 260 of plane. But, as molecule surface is stronger on GaAs(110) than on Au(111), TTB-  
 261 AB cannot diffuse on the surface and the network can no longer be re-organized to  
 262 become once again compact. Therefore, after a first TTB-AB photo-isomerization,  
 263 TTB-AB neighboring molecules can be more easily isomerized because local steric  
 264 hindrance has decreased.



**Fig. 14** TTB-AB photo-isomerization on GaAs(110) surface. The same TTB-AB molecular island is shown **a** before and **b** after an 18 h exposure to UV irradiation at 375 nm and  $92 \text{ mW/cm}^2$  ( $V_s = -2.0 \text{ V}$ ,  $I_t = 25 \text{ pA}$ ). Molecules in the *cis* configuration appear to have one brighter lobe and occur in 1D stripes, as indicated by blue arrows. White scale bar, 10 nm. Reprinted with permission from [54]

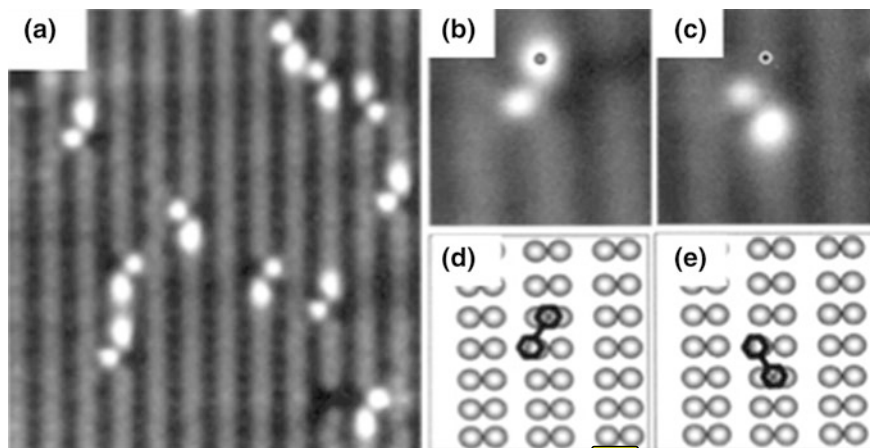
To conclude, azobenzene derivatives switching on semiconductors are strongly dependent on the molecule-substrate interactions. The switching can be quenched, like on Ag/Ge(111)- $\sqrt{3} \times \sqrt{3}$  or used to form stripes, like on GaAs(110) or to form enantiomers, and like on Si(111)-B.

## 4.2 Molecular Bistability Induced by Adsorption on Semiconductors

In the previous paragraph, we described changes in the photomechanical properties of intrinsic bistable molecules after their adsorption on a semiconductor. Here, we propose to discuss the design of molecular bistability induced by the presence of the surface.

Dujardin et al. [56, 57] have investigated the induced bistability of biphenyl molecules on a Si(100) surface. Biphenyl is based on two phenyl groups linked by a single C–C bond. This molecule has no intrinsic bistability in solution, in solid state, or in gas phase. However, when biphenyl molecules are deposited at room temperature on a Si(100)-2 $\times$ 1 surface and observed by STM at 5 K, they can be adsorbed with one of the two phenyl rings covalently linked with a silicon adatom of the surface, the second phenyl ring being covalently linked with two silicon adatoms (i.e., a butterfly configuration, Fig. 15a, d for the corresponding structural model). This strongly chemisorbed configuration is stable because no motion is observed from 5 to 300 K.

In the case of p-type boron-doped silicon surface, biphenyl molecules can be switched with tunneling electrons by applying a negative surface pulse voltage of

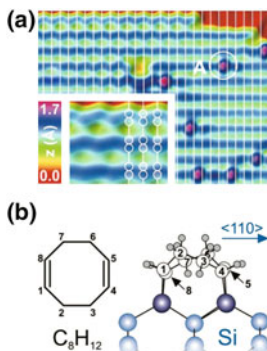


**Fig. 15** **a** STM image of biphenyl molecules on a Si(100)- $2 \times 1$  surface at 5 K ( $9 \times 9 \text{ nm}^2$ ,  $V_s = -2.0 \text{ V}$ ,  $I_t = 200 \text{ pA}$ ). **b** Zoom ( $2.1 \times 2.1 \text{ nm}^2$ ) of STM image shown in **a** showing a single biphenyl molecule in a stable configuration. The STM position for surface voltage pulse is indicated by a dot. **c** STM image of the same zone showing in **b** recorded after the surface voltage pulse. **d** and **e** Superimposed structural model of, respectively, **b** and **c**. Reprinted with permission from [56]

–3 V on adsorbed molecules (Fig. 15b–e). The mechanism of this switching has been deeply investigated [56]. For the first time, an electronic excitation process, based on the resonant transfer of one electron from the biphenyl HOMO to the STM tip, has been fully demonstrated [56]. As the process implies a charged transient oxidative state of biphenyl molecule (i.e., due to the loss of one electron), the nature of the doped, p or n, silicon substrate is relevant. The electronic excitation and relaxation processes are not modified by changing p-doping to n-doping. Nevertheless, the dynamics of switching is strongly altered. Indeed, the transient state is negatively charged (due to charge delocalization on molecule), leading to a strong repulsive interaction with n-doped silicon surface instead of attractive interaction with p-doped silicon surface [57]. This example proves the role of the molecule–surface interaction for the development of nanomachines on semiconductor surfaces. Biphenyl molecules adsorption on Si(100)- $2 \times 1$  leads to other exotic bistable configurations which can be thermally activated [58].

Adsorption of 1,5-cyclooctadiene (COD) on a Si(001)- $2 \times 1$  surface at 7 K was investigated by STM experiments [59–61]. Free COD molecules are prochiral; therefore, COD adsorption on a Si(001) surface leads prevalently to the formation of two degenerate configurations, corresponding to a bridge structure, where the two C=C bonds are involved in a [2 + 2] cycloaddition reaction with two silicon dimers of the surface, as supported by DFT calculations [62] (Fig. 16a).

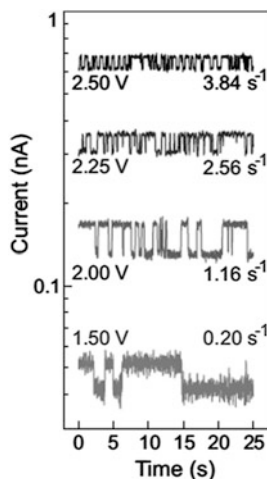
Time spectroscopy of the tunnel current under standard experimental setup (feedback loop turned off and STM tip at a fixed distance over adsorbed COD molecule) shows a random telegraph signal with an on–off ratio of 1.2:1 in (Fig. 17). Additional experiments were performed to determine the switching process.



**Fig. 16** **a** STM image of a COD molecule on a Si(001) surface at 7 K ( $10 \times 8 \text{ nm}^2$ ,  $V_s = -2.0 \text{ V}$ ,  $I_t = 600 \text{ pA}$ ). The *inset* ( $3 \times 2 \text{ nm}^2$ ) shows the Si dimer buckling at the upper step edge serving as a marker for the dimer position within a row. **b** COD molecule and structural model of the bridge structure. Reprinted with permission from [58]




**Fig. 17** Binary current fluctuations detected when tunneling through a COD molecule adsorbed in the bridge structure at a constant tip height (set point  $I_t = 150 \text{ pA}$ ,  $V_s = +2 \text{ V}$ ). The switching rate obtained for each current trace is indicated. Reprinted with permission from [59]

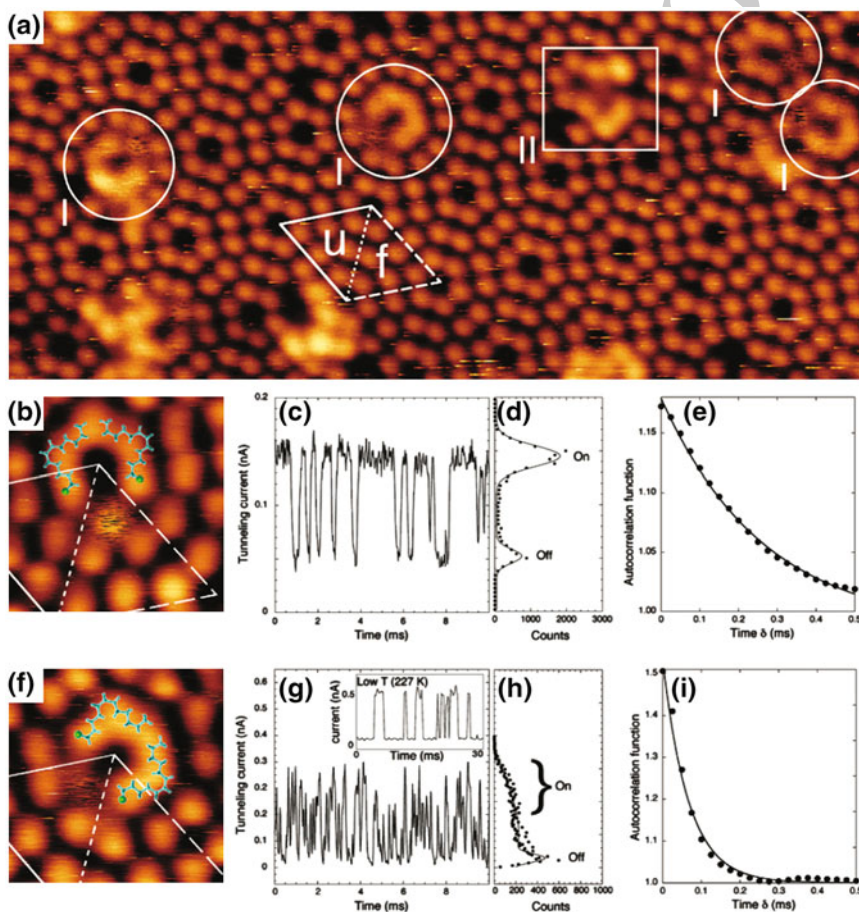




311 On the basis of experimental results, Nacci et al. proposed that COD switching  
 312 between two degenerate configurations is triggered by an inelastic single electron  
 313 process. This process is fully reversible and is achieved without any bond breaking  
 314 or reforming, a case that remains rare in the literature.

### 315 4.3 Adatom Bistability Induced by Adsorption of a Molecule

316 Adsorption of a molecule on a semiconductor surface can induce the modification  
 317 of molecular properties leading to molecular bistability, as described in the previous

318 section. In this last part, we propose to describe the switching of an adatom (of the  
 319 surface) induced by molecular adsorption. Polanyi  [63, 64] have investigated  
 320 the adsorption of chlorododecane on the Si(111)-7  $\times$  7 surface. These molecules are  
 321 non-covalently adsorbed on the surface. Pairs of chlorododecane molecules are self-  
 322 assembled into two types of dimers, forming a corral surrounding a silicon corner  
 323 hole or a corner adatom (respectively, I and II in Fig. 18).



**Fig. 18** **a** STM image (room temperature,  $23 \times 10$    $V_s = 2.0$  V,  $I_t = 100$  pA) of chlorododecane molecules adsorbed on a Si(111)-7  $\times$  7 surface with two types of dimers surrounding a  corner hole (*type I*) or corner adatom (*type II*). Faulted (*f*) and unfaulted (*u*) half-cells of Si(111)-7  $\times$  7 are marked. **b** High resolution STM image ( $3 \times 3$  nm<sup>2</sup>,  $V_s = 2.5$  V,  $I_t = 400$  pA) of *type I* corral with superimposed structural model. **c** Tunneling current versus time measurements over a faulted corralled adatom (shown in **b**) at  $V_s = +2.5$  V. **d** The corresponding tunneling current distribution with a pair of Gaussian functions fitted. High-current (on) and low-current (off) states are labeled. **e** The autocorrelation of the tunneling current time trace of **c**. Reprinted with permission from [64]




When a pair of chlorododecane molecules surrounds a corner hole, a corner adatom, located between jaws of the corral, remains uncovered (Fig. 18b). This adatom exhibits a streaky appearance, corresponding to a switching between conductance states. This can be demonstrated by recording the tunneling current versus time (Fig. 18c–e). This switching has been interpreted as a single-atom electronic switch due to molecularly induced field effect. Small changes in the configuration of self-assembled pairs of chlorododecane molecules, which are dipoles, have a large electronic effect leading to high and low conductance. This interpretation is supported by DFT calculations. This is a new route toward molecular nanoelectronics induced by the adsorption of molecules on a silicon surface.

## 5 Conclusion and Perspectives

The development of single molecular machines on semiconductors is still a challenge. Some proofs of concepts have been successfully achieved. Molecule–surface interactions play a key role in this field because molecular motion is strongly conditioned by the molecule–surface interactions. In terms of perspective, semiconductors could be used as templates to guide molecular motions and to develop devices operating at room temperature.

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

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Change to italics	— under matter to be changed	↵
Change to capitals	≡ under matter to be changed	≡
Change to small capitals	≡ under matter to be changed	≡
Change to bold type	~ under matter to be changed	~
Change to bold italic	≈ under matter to be changed	≈
Change to lower case	Encircle matter to be changed	≡
Change italic to upright type	(As above)	⊕
Change bold to non-bold type	(As above)	⊖
Insert 'superior' character	/ through character or ∧ where required	Υ or Υ under character e.g. Υ or Υ
Insert 'inferior' character	(As above)	∧ over character e.g. ∧
Insert full stop	(As above)	⊙
Insert comma	(As above)	,
Insert single quotation marks	(As above)	Ƴ or ƴ and/or Ƶ or ƶ
Insert double quotation marks	(As above)	ƴ or ƶ and/or Ƶ or ƶ
Insert hyphen	(As above)	⊥
Start new paragraph	┌	┌
No new paragraph	┐	┐
Transpose	└┐	└┐
Close up	linking ○ characters	Ⓞ
Insert or substitute space between characters or words	/ through character or ∧ where required	Υ
Reduce space between characters or words		↑